

PRIORITY Serial No. 10/017,557
PRIORITY Filing Date: 12/14/2001
Inventor: Schuegraf et. al.
PRIORITY Examiner Trung Q. Dang
PRIORITY Group Art Unit 2823
Assignee: Micron Technology, Inc.
Title: Methods of Forming Circuitry

INFORMATION DISCLOSURE STATEMENT

PURSUANT TO 37 C.F.R. §§1.56, 1.97 AND 1.98

In compliance with 37 C.F.R. §§1.56, 1.97 and 1.98, your attention is directed to the United States patents and other references listed on the attached Form PTO-1449.

The listed references were cited by, or submitted to, the Office in the parent, co-pending application of the above-identified application. The above-identified application is a continuation of co-pending application Serial No. 10/017,5570 filed December 14, 2001. Such prior disclosure is sufficient for the above-identified application as far as copies of the references are concerned. 37 C.F.R. §1.98(d) and MPEP §609(2). No admission is made regarding whether all the submitted references are prior art.

Citation of these references is respectfully requested.

Respectfully submitted,

Dated: 9/30/03

Attorney: 

David G. Latwesen, Ph.D. Reg. #38,533
WELLS ST. JOHN P.S.

Form PTO-1449		U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE		ATTY. DOCKET NO. MI22-2410		PRIORITY SERIAL NO. 10/017,557	
LIST OF ART CITED BY APPLICANT (Use several sheets if necessary)				APPLICANT Micron Technology, Inc.			
				PRIORITY FILING DATE 12/14/2001		PRIORITY GROUP 2823	
U.S. PATENT DOCUMENTS							
*Examiner Initial		Document Number	Date	Name	Class	Subclas s	Filing Date If Appropriate
	AA	6,104,053	8/00	Nagai			
	AB	5,998,251	12/99	Wu et al.			
	AC	5,414,655	5/95	Ozaki et al.			
	AD	5,981,369	11/99	Yoshida et al.			
	AE	6,281,540	8/01	Aoki			
	AF	6,130,449	10/00	Matsuoka			
	AG	4,907,046	3/90	Ohji et al.			
	AH	6,107,139	8/00	Tu et al.			
	AI	6,333,225	12/01	Schuegraf et al.			
	AJ						
FOREIGN PATENT DOCUMENTS							
		Document Number	Date	Country	Class	Subclas s	Translation
							Yes No
	AK	0 889 519 A2		EPO			
	AL						
OTHER REFERENCES (including Author, Title, Date, Pertinent Pages, Etc.)							
	AM		Kwon, K., et al., <i>Ta205 Capacitors for 1 Gbit DRAM and Beyond</i> ; 1994 IEEE, pp. 34.2.1-34.2.4				
	AN		Sun, S., et al., <i>A New CVD Tungsten Nitride Diffusion Barrier for Cu Interconnection</i> ; 1996 Symposium on VLSI Technology Digest of Technical Papers, pp. 46-47				
	AO						
	AP						
EXAMINER				DATE CONSIDERED			
<small>*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.</small>							